

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-54151736
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

LOW-POWER RS-485 TRANSCEIVER

Available in Small MSOP-8 Package

FEATURES

- Available in Small MSOP-8 Package
- Meets or Exceeds the Requirements of the TIA/EIA-485A Standard
- Low Quiescent Power
 - 0.3 mA Active Mode
 - 1 nA Shutdown Mode
- 1/8 Unit Load—Up to 256 Nodes on a Bus
- Bus-Pin ESD Protection Up to 15 kV
- Industry-Standard SN75176 Footprint
- Failsafe Receiver (Bus Open, Bus Shorted, Bus Idle)

APPLICATIONS

- Energy Meter Networks
- Motor Control
- Power Inverters
- Industrial Automation
- Building Automation Networks
- Battery-Powered Applications
- Telecommunications Equipment

DESCRIPTION

These devices are half-duplex transceivers designed for RS-485 data bus networks. Powered by a 5-V supply, they are fully compliant with TIA/EIA-485A standard. With controlled transition times, these devices are suitable for transmitting data over long twisted-pair cables. SN65HVD3082E and SN75HVD3082E devices are optimized for signaling rates up to 200 kbps. SN65HVD3085E is suitable for data transmission up to 1 Mbps, whereas SN65HVD3088E is suitable for applications requiring signaling rates up to 20 Mbps. These devices are designed to operate with very low supply current, typically 0.3 mA, exclusive of the load. When in the inactive shutdown mode, the supply current drops to a few nanoamps, making these devices ideal for power-sensitive applications.

The wide common-mode range and high ESD protection levels of these devices make them suitable for demanding applications such as energy meter networks, electrical inverters, status/command signals across telecom racks, cabled chassis interconnects, and industrial automation networks where noise tolerance is essential. These devices match the industry-standard footprint of SN75176. Power-on reset circuits keep the outputs in a high-impedance state until the supply voltage has stabilized. A thermal shutdown function protects the device from damage due to system fault conditions. The SN75HVD3082E is characterized for operation from 0°C to 70°C and SN65HVD308xE are characterized for operation from –40°C to 85°C air temperature.

ORDERING INFORMATION

T _A	SIGNALING RATE (Mbps)	PACKAGE TYPE		
		P	D(1)	DGK(2)
0°C to 70°C	0.2	SN75HVD3082EP Marked as 75HVD3082	SN75HVD3082ED Marked as VN3082	SN75HVD3082EDGK Marked as NWM
–40°C to 85°C	0.2	SN65HVD3082EP Marked as 65HVD3082	SN65HVD3082ED Marked as VP3082	SN65HVD3082EDGK Marked as NWN
	1		SN65HVD3085ED Marked as VP3085	SN65HVD3085EDGK Marked as NWK
	20		SN65HVD3088ED Marked as VP3088	SN65HVD3088EDGK Marked as NWH

(1) The D package is available taped and reeled. Add an R suffix to the device type (i.e., SN65HVD3082EDR).

(2) The DGK package is available taped and reeled. Add an R suffix to the device type (i.e., SN65HVD3082EDGKR).



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range unless otherwise noted⁽¹⁾ (2)

	UNITS
Supply voltage range, V_{CC}	–0.5 V to 7 V
Voltage range at A or B	–9 V to 14 V
Voltage range at any logic pin	–0.3 V to $V_{CC} + 0.3$ V
Receiver output current	–24 mA to 24 mA
Voltage input range, transient pulse, A and B, through 100 Ω (see Figure 13)	–50 V to 50 V
Junction temperature, T_J	170°C
Continuous total power dissipation	Refer to Package Dissipation Table

(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.

PACKAGE DISSIPATION RATINGS

PACKAGE	JEDEC BOARD MODEL	$T_A < 25^\circ\text{C}$ POWER RATING	DERATING FACTOR ⁽³⁾ ABOVE $T_A = 25^\circ\text{C}$	$T_A = 70^\circ\text{C}$ POWER RATING	$T_A = 85^\circ\text{C}$ POWER RATING
D	Low k ⁽¹⁾	507 mW	4.82 mW/°C	289 mW	217 mW
	High k ⁽²⁾	824 mW	7.85 mW/°C	471 mW	353 mW
P	Low k ⁽¹⁾	686 mW	6.53 mW/°C	392 mW	294 mW
DGK	Low k ⁽¹⁾	394 mW	3.76 mW/°C	255 mW	169 mW
	High k ⁽²⁾	583 mW	5.55 mW/°C	333 mW	250 mW

(1) In accordance with the low-k thermal metric definitions of EIA/JESD51-3

(2) In accordance with the high-k thermal metric definitions of EIA/JESD51-7

(3) This is the inverse of the junction-to-ambient thermal resistance when board-mounted and with no air flow.

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RECOMMENDED OPERATING CONDITIONS⁽¹⁾

		MIN	TYP	MAX	UNIT
Supply voltage, V_{CC}		4.5		5.5	V
Input voltage at any bus terminal (separately or common mode), V_I		-7		12	V
High-level input voltage (D, DE, or \overline{RE} inputs), V_{IH}		2		V_{CC}	V
Low-level input voltage (D, DE, or \overline{RE} inputs), V_{IL}		0		0.8	V
Differential input voltage, V_{ID}		-12		12	V
Output current, I_O	Driver	-60		60	mA
	Receiver	-8		8	
Differential load resistance, R_L		54	60		Ω
Signaling rate, $1/t_{UI}$	SN65HVD3082E, SN75HVD3082E			0.2	Mbps
	SN65HVD3085E			1	
	SN65HVD3088E			20	
Operating free-air temperature, T_A	SN65HVD3082E, SN65HVD3085E, SN65HVD3088E	-40		85	$^{\circ}\text{C}$
	SN75HVD3082E	0		70	
Junction temperature, T_J ⁽²⁾		-40		130	$^{\circ}\text{C}$

(1) The algebraic convention, in which the least positive (most negative) limit is designated as minimum, is used in this data sheet.

(2) See *thermal characteristics* table for information on maintenance of this specification for the DGK package.

SUPPLY CURRENT

over recommended operating conditions unless otherwise noted

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
I_{CC}	Driver and receiver enabled	D at V_{CC} or open, DE at V_{CC} , RE at 0 V, No load		425	900	μA
	Driver enabled, receiver disabled	D at V_{CC} or open, DE at V_{CC} , RE at V_{CC} , No load		330	600	μA
	Receiver enabled, driver disabled	D at V_{CC} or open, DE at 0 V, RE at 0 V, No load		300	600	μA
	Driver and receiver disabled	D at V_{CC} or open, DE at 0 V, RE at V_{CC}		0.001	2	μA

(1) All typical values are at 25 $^{\circ}\text{C}$ and with a 5-V supply.

ELECTROSTATIC DISCHARGE PROTECTION

PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
Human body model	Bus terminals and GND		± 15		kV
Human body model ⁽²⁾	All pins		± 4		kV
Charged-device-model ⁽³⁾	All pins		± 1		kV

(1) All typical values at 25 $^{\circ}\text{C}$

(2) Tested in accordance with JEDEC Standard 22, Test Method A114-A.

(3) Tested in accordance with JEDEC Standard 22, Test Method C101.

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DRIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions unless otherwise noted

PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
V_{OD} Differential output voltage	$I_O = 0$, No load	3	4.3		V
	$R_L = 54 \Omega$, See Figure 1	1.5	2.3		
	$R_L = 100 \Omega$	2			
	$V_{TEST} = -7 \text{ V to } 12 \text{ V}$, See Figure 2	1.5			
ΔV_{OD} Change in magnitude of differential output voltage	See Figure 1 and Figure 2	-0.2	0	0.2	V
$V_{OC(SS)}$ Steady-state common-mode output voltage	See Figure 3	1	2.6	3	V
$\Delta V_{OC(SS)}$ Change in steady-state common-mode output voltage		-0.1	0	0.1	
$V_{OC(PP)}$	See Figure 3		500		mV
I_{OZ} High-impedance output current	See receiver input currents				μA
I_I Input current	D, DE	-100		100	
I_{OS} Short-circuit output current	$-7 \text{ V} \leq V_O \leq 12 \text{ V}$, See Figure 7	-250		250	mA

(1) All typical values are at 25°C and with a 5V-supply.

DRIVER SWITCHING CHARACTERISTICS

over recommended operating conditions unless otherwise noted

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH} Propagation delay time, low-to-high-level output	$R_L = 54 \Omega$, $C_L = 50 \text{ pF}$, See Figure 4	HVD3082E	700	1300	ns
t_{PHL} Propagation delay time, high-to-low-level output		HVD3085E	150	500	
		HVD3088E	12	20	
t_r Differential output signal rise time	$R_L = 54 \Omega$, $C_L = 50 \text{ pF}$, See Figure 4	HVD3082E	500	900	ns
t_f Differential output signal fall time		HVD3085E	200	300	
		HVD3088E	7	15	
$t_{sk(p)}$ Pulse skew ($ t_{PHL} - t_{PLH} $)	$R_L = 54 \Omega$, $C_L = 50 \text{ pF}$, See Figure 4	HVD3082E	20	200	ns
		HVD3085E	5	50	
		HVD3088E	1.4	5	
t_{PZH} Propagation delay time, high-impedance-to-high-level output	$R_L = 110 \Omega$, R_E at 0 V, See Figure 5 and Figure 6	HVD3082E	2500	7000	ns
t_{PZL} Propagation delay time, high-impedance-to-low-level output		HVD3085E	1000	2500	
		HVD3088E	13	30	
t_{PHZ} Propagation delay time, high-level-to-high-impedance output	$R_L = 110 \Omega$, R_E at 0 V, See Figure 5 and Figure 6	HVD3082E	80	200	ns
t_{PLZ} Propagation delay time, low-level-to-high-impedance output		HVD3085E	60	100	
		HVD3088E	12	30	
$t_{PZH(SHDN)}$ Propagation delay time, shutdown-to-high-level output	$R_L = 110 \Omega$, \overline{RE} at V_{CC} , See Figure 5	HVD3082E	3500	7000	ns
$t_{PZL(SHDN)}$ Propagation delay time, shutdown-to-low-level output		HVD3085E	2500	4500	
		HVD3088E	1600	2600	

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RECEIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions unless otherwise noted

PARAMETER	TEST CONDITIONS	MIN	TYP(1)	MAX	UNIT
V_{IT+} Positive-going input threshold voltage	$I_O = -8 \text{ mA}$		-85	-10	mV
V_{IT-} Negative-going input threshold voltage	$I_O = 8 \text{ mA}$	-200	-115		mV
V_{hys} Hysteresis voltage ($V_{IT+} - V_{IT-}$)			30		mV
V_{OH} High-level output voltage	$V_{ID} = 200 \text{ mV}$, $I_{OH} = -8 \text{ mA}$, See Figure 8	4	4.6		V
V_{OL} Low-level output voltage	$V_{ID} = -200 \text{ mV}$, $I_{OH} = 8 \text{ mA}$, See Figure 8		0.15	0.4	V
I_{OZ} High-impedance-state output current	$V_O = 0$ to V_{CC} , $\overline{RE} = V_{CC}$	-1		1	μA
I_I Bus input current	$V_{IH} = 12 \text{ V}$, $V_{CC} = 5 \text{ V}$		0.04	0.1	mA
	$V_{IH} = 12 \text{ V}$, $V_{CC} = 0$		0.06	0.125	
	$V_{IH} = -7 \text{ V}$, $V_{CC} = 5 \text{ V}$	-0.1	-0.04		
	$V_{IH} = -7 \text{ V}$, $V_{CC} = 0$	-0.05	-0.03		
I_{IH} High-level input current (\overline{RE})	$V_{IH} = 2 \text{ V}$	-60	-30		μA
I_{IL} Low-level input current (\overline{RE})	$V_{IL} = 0.8 \text{ V}$	-60	-30		μA
C_{diff} Differential input capacitance	$V_I = 0.4 \sin(4E6\pi t) + 0.5 \text{ V}$, DE at 0 V		7		pF

(1) All typical values are at 25°C and with a 5-V supply.

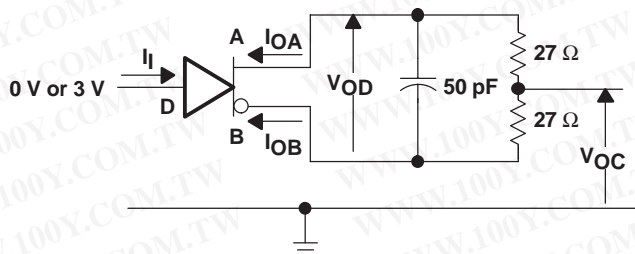
RECEIVER SWITCHING CHARACTERISTICS

over recommended operating conditions unless otherwise noted

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH} Propagation delay time, low-to-high-level output	$R_L = 54 \Omega$, $C_L = 15 \text{ pF}$, See Figure 9		75	200	ns
t_{PHL} Propagation delay time, high-to-low-level output	$R_L = 54 \Omega$, $C_L = 15 \text{ pF}$, See Figure 9		79	200	ns
$t_{sk(p)}$ Pulse skew ($ t_{PHL} - t_{PLH} $)	$R_L = 54 \Omega$, $C_L = 15 \text{ pF}$, See Figure 9		4	30	ns
t_r Output signal rise time	$V_{ID} = -1.5 \text{ V}$ to 1.5 V , $C_L = 15 \text{ pF}$, See Figure 9		1.5	3	ns
t_f Output signal fall time					
t_{PZH} Output enable time to high level	$C_L = 15 \text{ pF}$, DE at 3 V, See Figure 10 and Figure 11		5	50	ns
				30	
t_{PZL} Output enable time to low level			10	50	ns
				30	
t_{PHZ} Output enable time from high level			5	50	ns
				30	
t_{PLZ} Output enable time from low level			8	50	ns
				30	
$t_{PZH(SHDN)}$ Propagation delay time, shutdown-to-high-level output			1600	3500	ns
$t_{PZL(SHDN)}$ Propagation delay time, shutdown-to-low-level output					

PARAMETER MEASUREMENT INFORMATION

NOTE: Test load capacitance includes probe and jig capacitance (unless otherwise specified). Signal generator characteristics: rise and fall time < 6 ns, pulse rate 100 kHz, 50% duty cycle. $Z_0 = 50\ \Omega$ (unless otherwise specified).



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Figure 1. Driver Test Circuit, V_{OD} and V_{OC} Without Common-Mode Loading

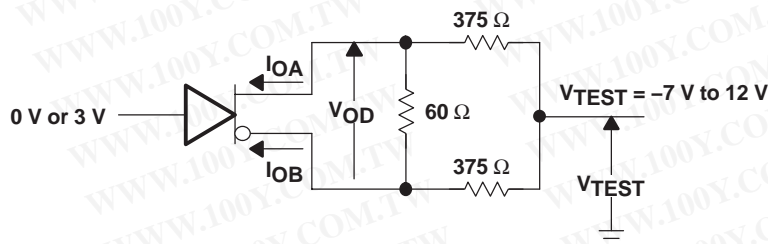


Figure 2. Driver Test Circuit, V_{OD} With Common-Mode Loading

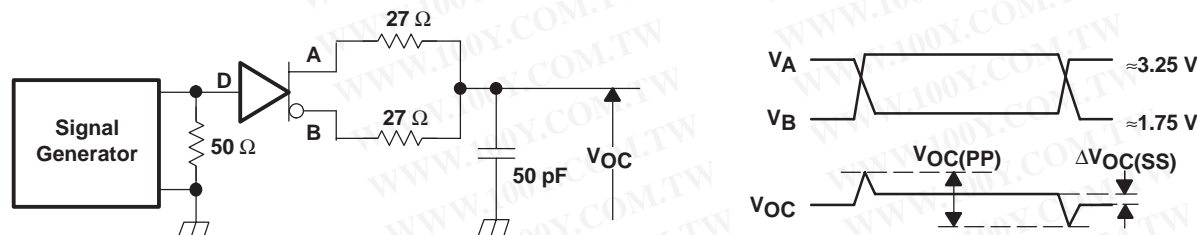


Figure 3. Driver V_{OC} Test Circuit and Waveforms

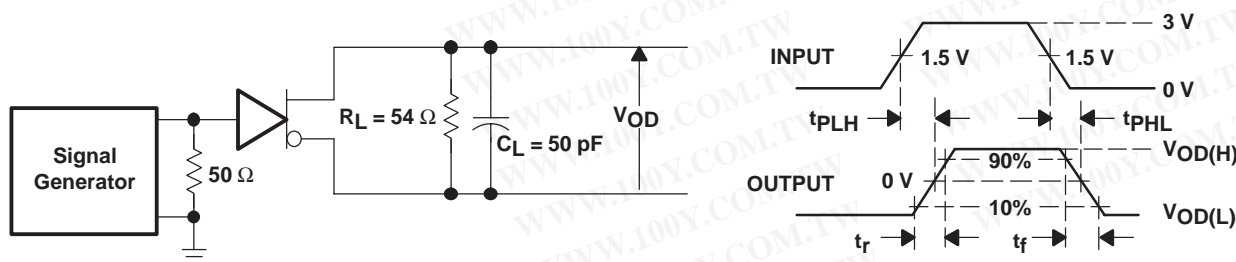


Figure 4. Driver Switching Test Circuit and Waveforms

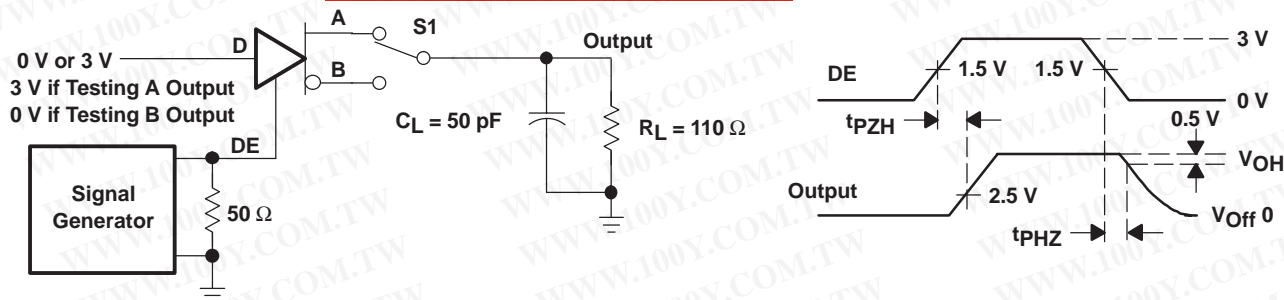


Figure 5. Driver Enable/Disable Test Circuit and Waveforms, High Output

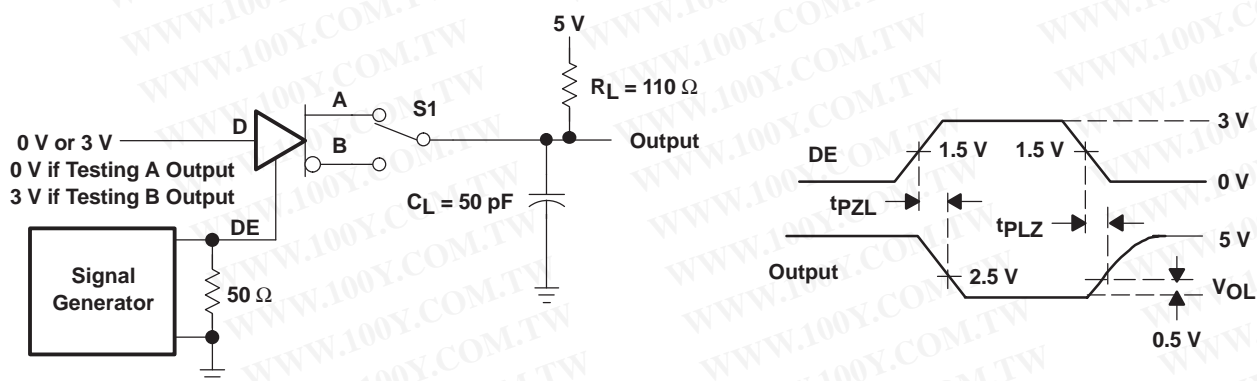


Figure 6. Driver Enable/Disable Test Circuit and Waveforms, Low Output

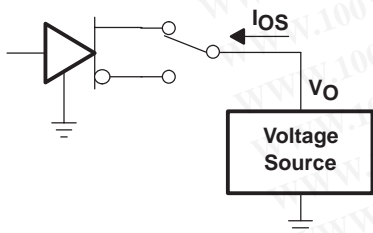


Figure 7. Driver Short-Circuit Test

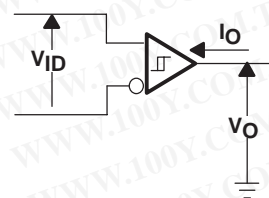


Figure 8. Receiver Parameter Definitions

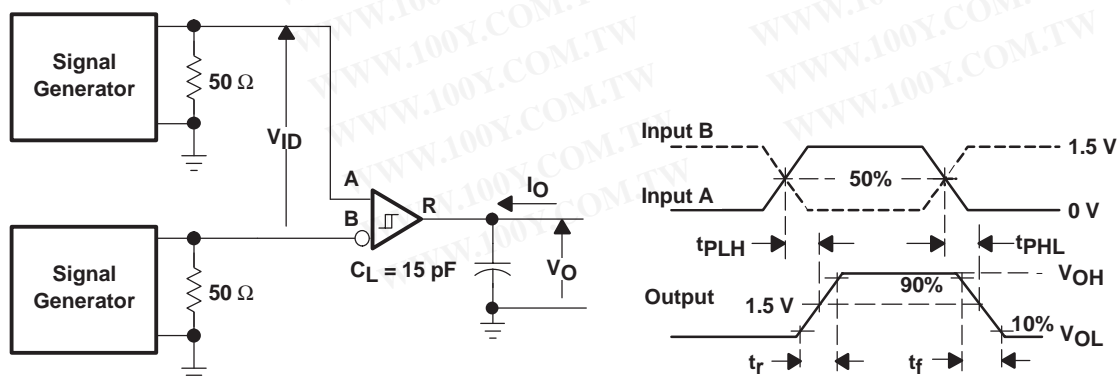


Figure 9. Receiver Switching Test Circuit and Waveforms

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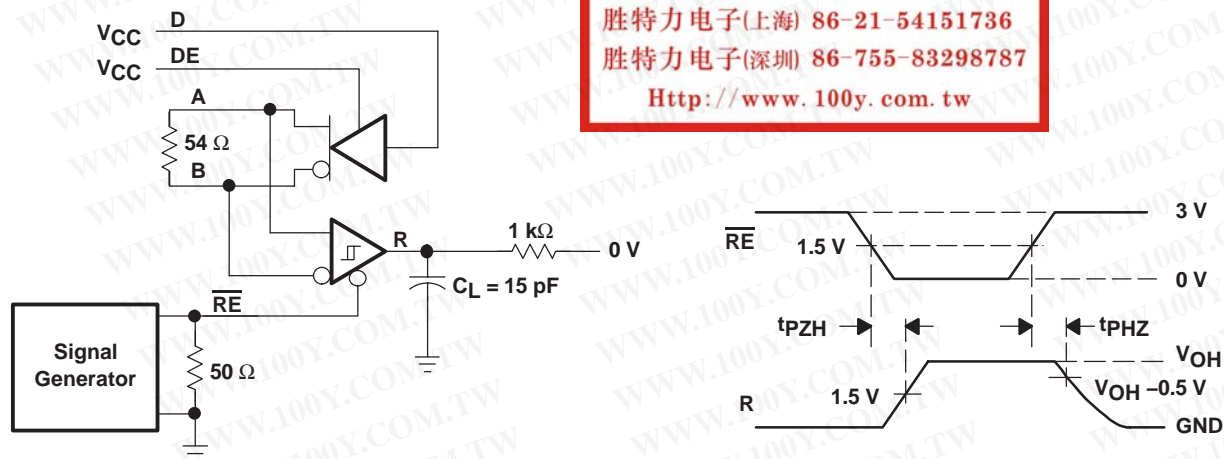


Figure 10. Receiver Enable/Disable Test Circuit and Waveforms, Data Output High

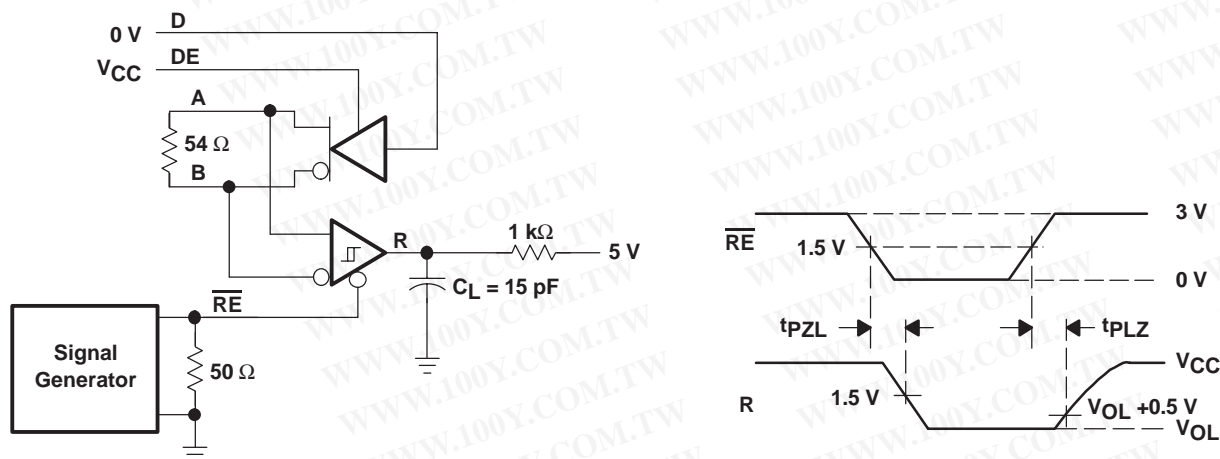


Figure 11. Receiver Enable/Disable Test Circuit and Waveforms, Data Output Low

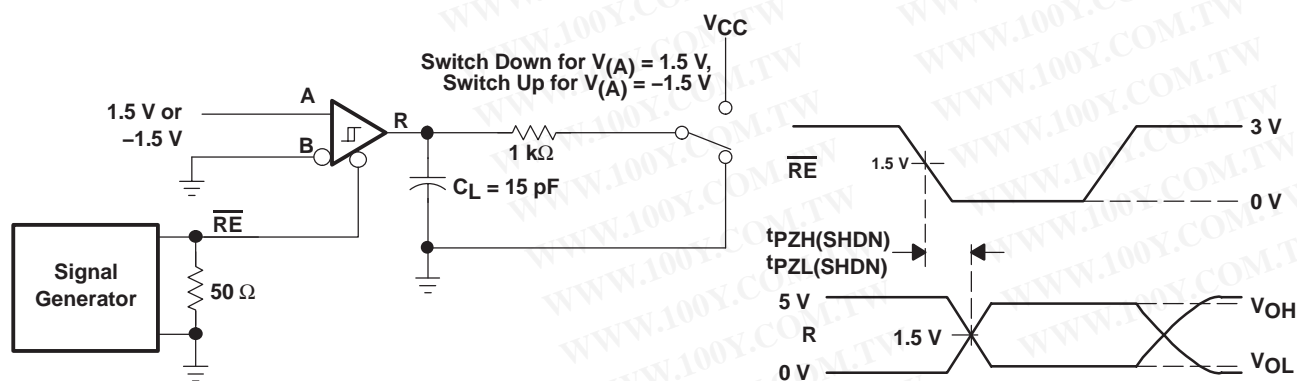


Figure 12. Receiver Enable From Shutdown Test Circuit and Waveforms

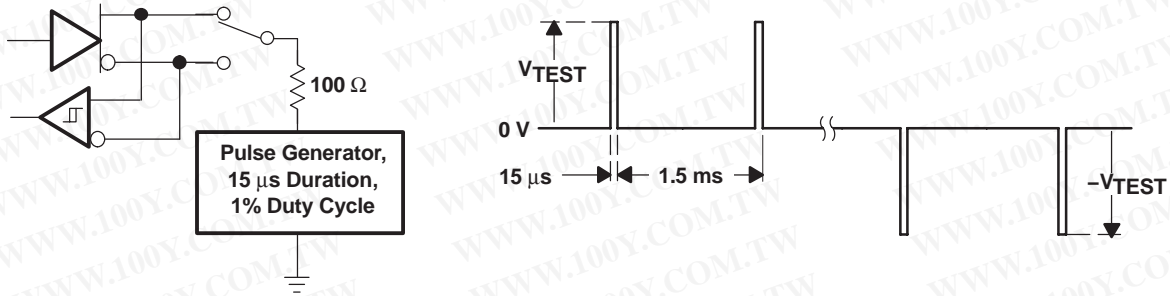
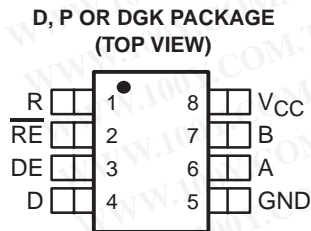


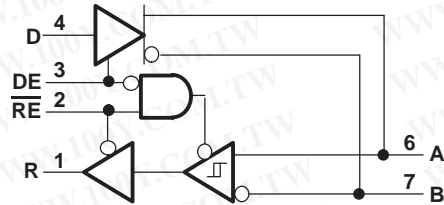
Figure 13. Test Circuit and Waveforms, Transient Over-Voltage Test

DEVICE INFORMATION

PIN ASSIGNMENTS



LOGIC DIAGRAM (POSITIVE LOGIC)



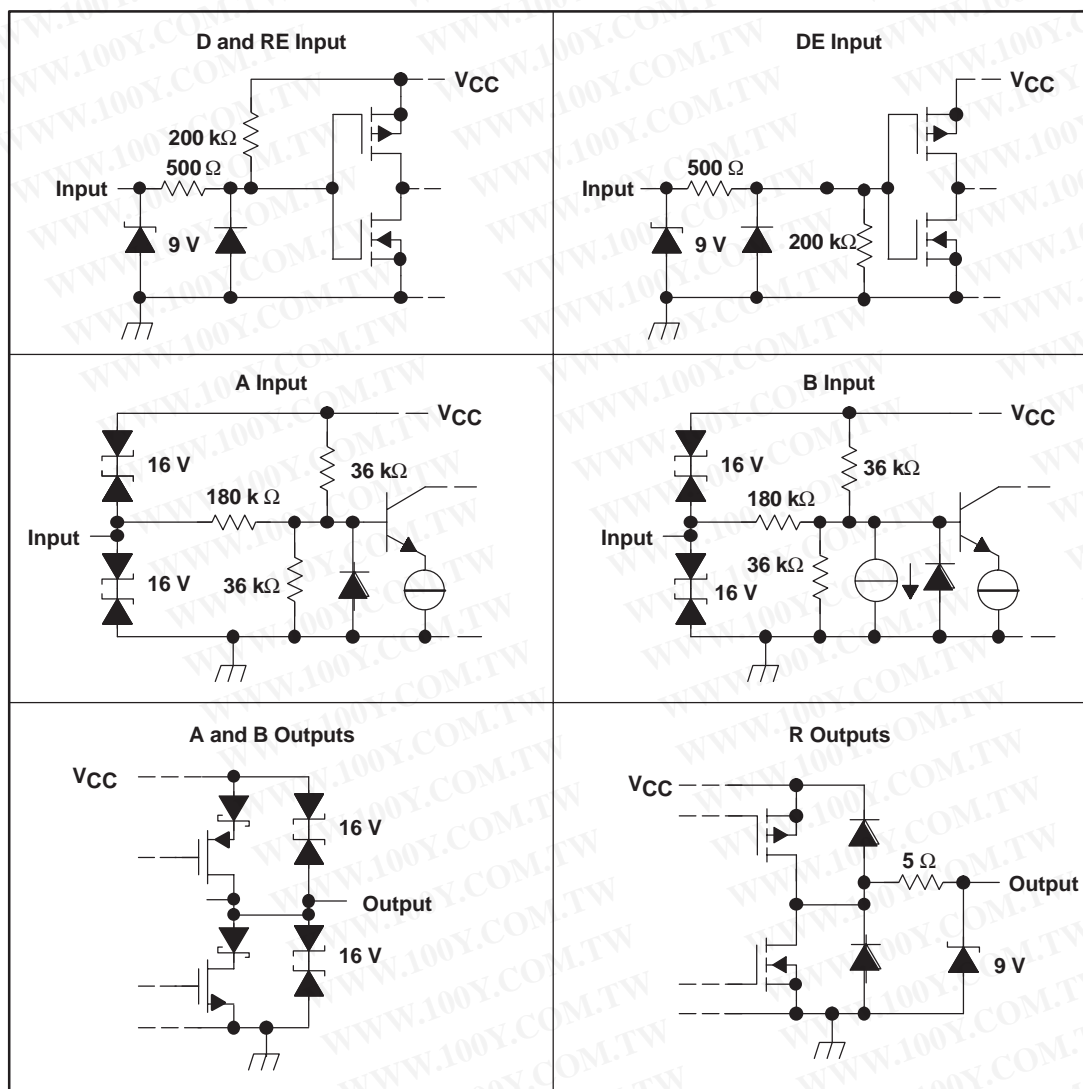
FUNCTION TABLE

DRIVER				RECEIVER		
INPUT D	ENABLE DE	OUTPUTS		DIFFERENTIAL INPUTS $V_{ID} = V_A - V_B$	ENABLE RE	OUTPUT R
		A	B			
H	H	H	L	$V_{ID} \leq -0.2 \text{ V}$	L	L
L	H	L	H	$-0.2 \text{ V} < V_{ID} < -0.01 \text{ V}$	L	?
X	L	Z	Z	$-0.01 \text{ V} \leq V_{ID}$	L	H
Open	H	H	L	X	H	Z
X	Open	Z	Z	Open circuit	L	H
				Short circuit	L	H
				X	Open	Z

NOTE: H= high level; L = low level; Z = high impedance; X = irrelevant; ? = indeterminate

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EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS



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DGK Package

THERMAL CHARACTERISTICS

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Θ_{JA} Junction-to-ambient thermal resistance ⁽¹⁾	Low-k ⁽²⁾ board, no air flow		266		°C/W
	High-k ⁽³⁾ board, no air flow		180		
Θ_{JB} Junction-to-board thermal resistance	High-k ⁽³⁾ board, no air flow		108		°C/W
Θ_{JC} Junction-to-case thermal resistance			66		
P(AVG) Average power dissipation	$R_L = 54 \Omega$, Input to D is a 200 kbps 50% duty cycle square wave V_{CC} at 5.5 V, $T_J = 130^\circ\text{C}$			203	mW
P(AVG) Average power dissipation	$R_L = 54 \Omega$, Input to D is a 1 Mbps 50% duty cycle square wave V_{CC} at 5.5 V, $T_J = 130^\circ\text{C}$			205	mW
P(AVG) Average power dissipation	$R_L = 54 \Omega$, Input to D is a 20 Mbps 50% duty cycle square wave V_{CC} at 5.5 V, $T_J = 130^\circ\text{C}$			276	mW
T_A Ambient air temperature	High k board model	–40		93	°C
	Low k board model	–40		75	
T_{SD} Thermal shut-down junction temperature			165		°C

(1) See TI application note literature number SZZA003, *Package Thermal Characterization Methodologies*, for an explanation of this parameter.

(2) JESD51-3 *Low Effective Thermal Conductivity Test Board for Leaded Surface Mount Packages*

(3) JESD51-7 *High Effective Thermal Conductivity Test Board for Leaded Surface Mount Packages*

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TYPICAL CHARACTERISTICS

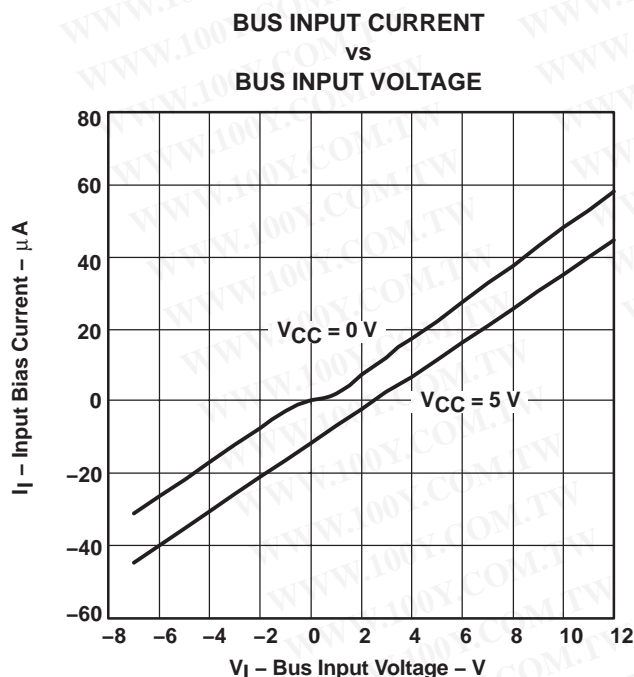


Figure 14

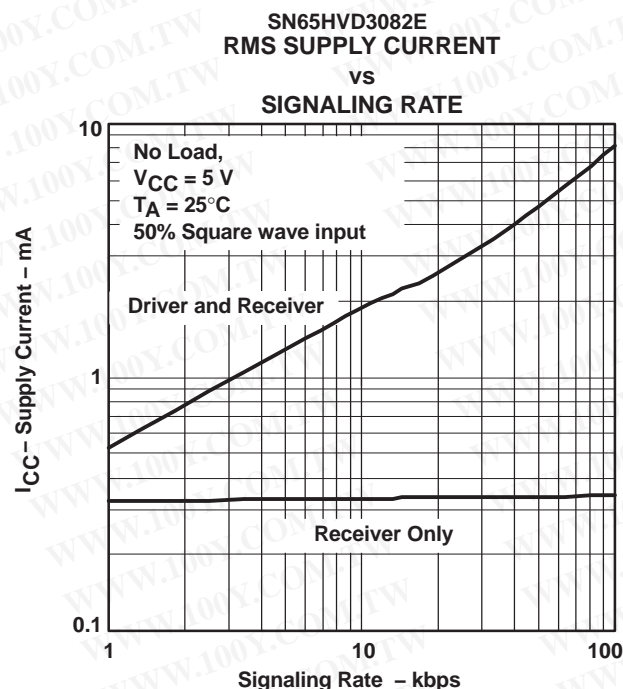


Figure 15

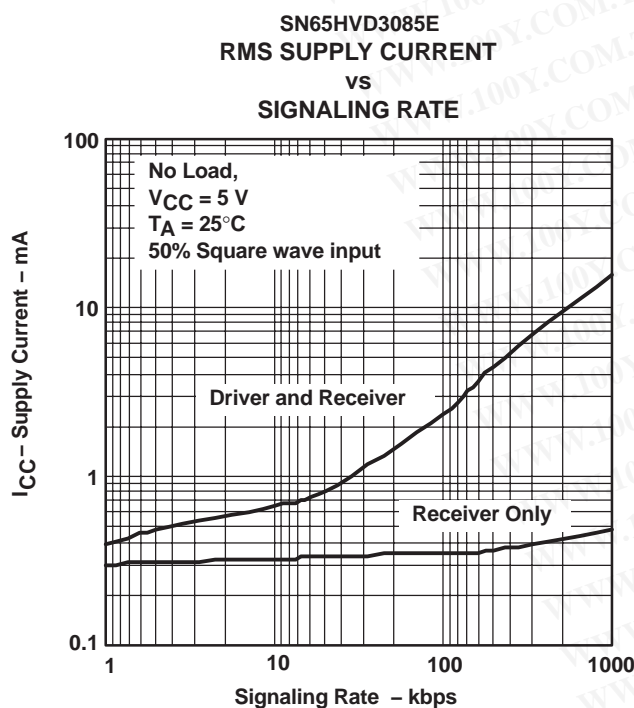


Figure 16

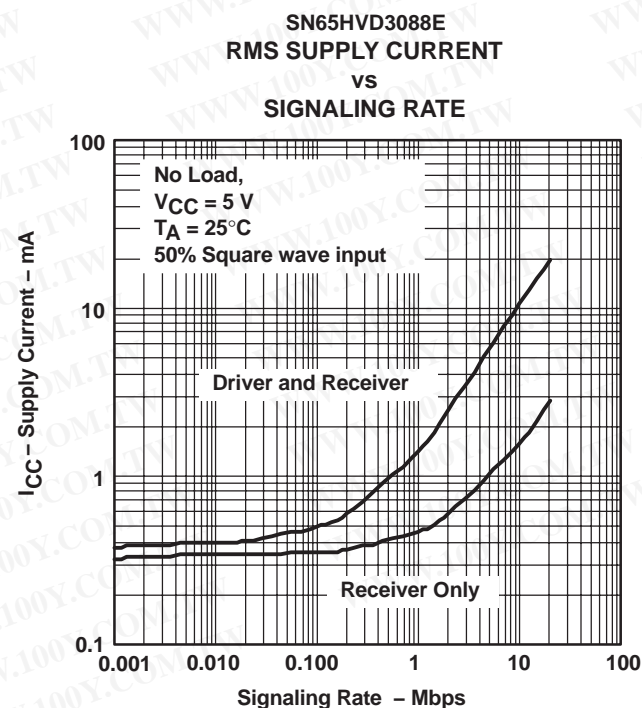


Figure 17

TYPICAL CHARACTERISTICS

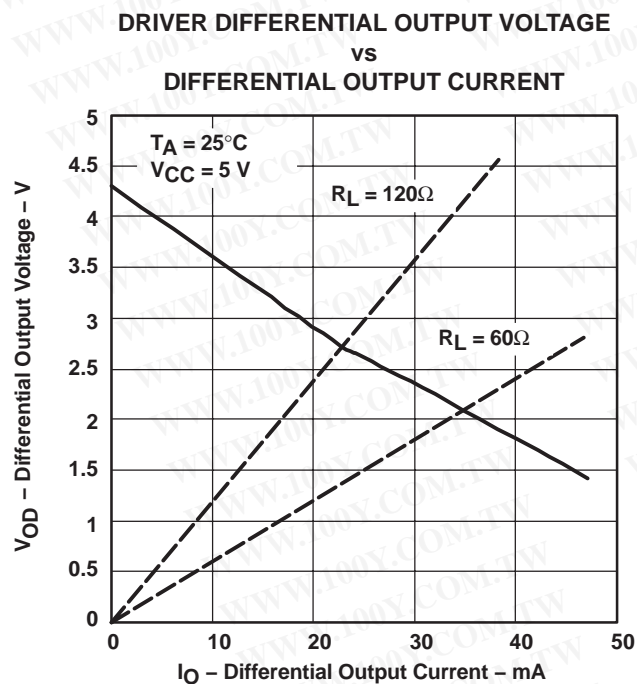


Figure 18

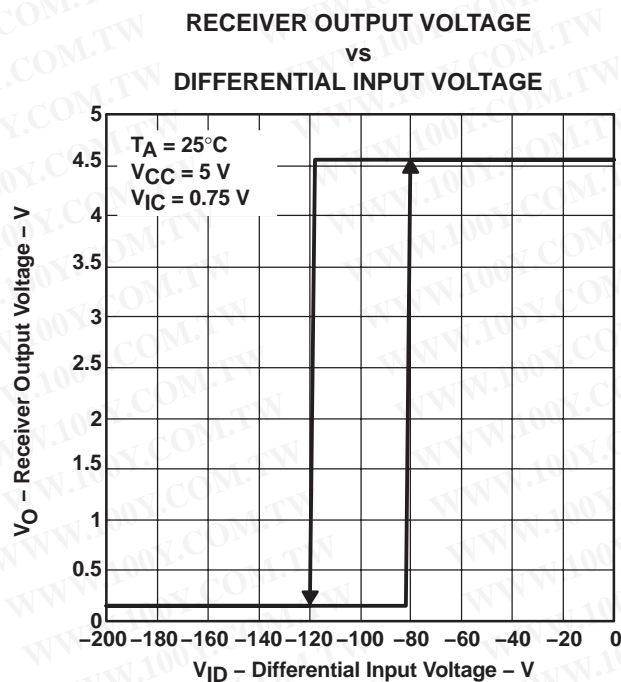
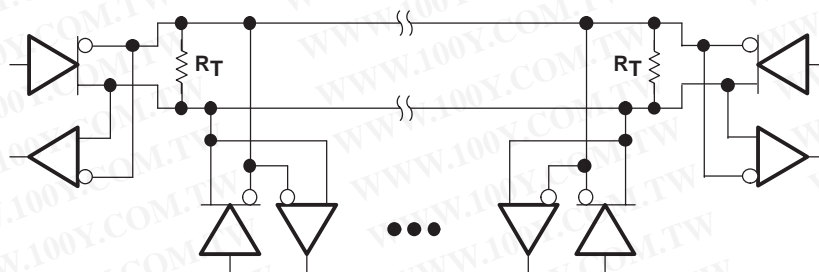


Figure 19

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APPLICATION INFORMATION



NOTE: The line should be terminated at both ends with its characteristic impedance ($R_T = Z_0$). Stub lengths off the main line should be kept as short as possible.

Figure 20. Typical Application Circuit

POWER USAGE IN AN RS-485 TRANSCEIVER

Power consumption is a concern in many applications. Power supply current is delivered to the bus load as well as to the transceiver circuitry. For a typical RS-485 bus configuration, the load that an active driver must drive consists of all of the receiving nodes, plus the termination resistors at each end of the bus.

The load presented by the receiving nodes depends on the input impedance of the receiver. The TIA/EIA-485-A standard defines a unit load as allowing up to 1 mA. With up to 32 unit loads allowed on the bus, the total current supplied to all receivers can be as high as 32 mA. The HVD308xE is rated as a 1/8 unit load device. As shown in Figure 14, the bus input current is less than 1/8 mA, allowing up to 256 nodes on a single bus.

The current in the termination resistors depends on the differential bus voltage. The standard requires active drivers to produce at least 1.5 V of differential signal. For a bus terminated with one standard 120-Ω resistor at each end, this sums to 25 mA differential output current whenever the bus is active. Typically the HVD308xE can drive more than 25 mA to a 60 Ω load, resulting in a differential output voltage higher than the minimum required by the standard. (See Figure 16.)

Overall, the total load current can be 60 mA to a loaded RS-485 bus. This is in addition to the current required by the transceiver itself; the HVD308xE circuitry requires only about 0.4 mA with both driver and receiver enabled, and only 0.3 mA with either the driver enabled or with the receiver enabled. In low-power shutdown mode, neither the driver nor receiver is active, and the supply current is very low.

Supply current increases with signaling rate primarily due to the totum pole outputs of the driver (see Figure 15). When these outputs change state, there is a moment when both the high-side and low-side output transistors are conducting and this creates a short spike in the supply current. As the frequency of state changes increases, more power is used.

LOW-POWER SHUTDOWN MODE

When both the driver and receiver are disabled (\overline{DE} low and \overline{RE} high) the device is in shutdown mode. If the enable inputs are in this state for less than 60 ns, the device does not enter shutdown mode. This guards against inadvertently entering shutdown mode during driver/receiver enabling. Only when the enable inputs are held in this state for 300 ns or more, the device is assured to be in shutdown mode. In this low-power shutdown mode, most internal circuitry is powered down, and the supply current is typically 1 nA. When either the driver or the receiver is re-enabled, the internal circuitry becomes active.

If only the driver is re-enabled (\overline{DE} transitions to high) the driver outputs are driven according to the D input after the enable times given by $t_{PZH(SHDN)}$ and $t_{PZL(SHDN)}$ in the driver switching characteristics. If the D input is open when the driver is enabled, the driver outputs defaults to A high and B low, in accordance with the driver failsafe feature.

If only the receiver is re-enabled (\overline{RE} transitions to low) the receiver output is driven according to the state of the bus inputs (A and B) after the enable times given by $t_{PZH(SHDN)}$ and $t_{PZL(SHDN)}$ in the receiver switching characteristics. If there is no valid state on the bus the receiver responds as described in the failsafe operation section.

If both the receiver and driver are re-enabled simultaneously, the receiver output is driven according to the state of the bus inputs (A and B) and the driver output is driven according to the D input. Note that the state of the active driver affects the inputs to the receiver. Therefore, the receiver outputs are valid as soon as the driver outputs are valid.

THERMAL CHARACTERISTICS OF IC PACKAGES

Θ_{JA} (Junction-to-Ambient Thermal Resistance) is defined as the difference in junction temperature to ambient temperature divided by the operating power

Θ_{JA} is NOT a constant and is a strong function of

- the PCB design (50% variation)
- altitude (20% variation)
- device power (5% variation)

Θ_{JA} can be used to compare the thermal performance of packages if the specific test conditions are defined and used. Standardized testing includes specification of PCB construction, test chamber volume, sensor locations, and the thermal characteristics of holding fixtures. Θ_{JA} is often misused when it is used to calculate junction temperatures for other installations.

TI uses two test PCBs as defined by JEDEC specifications. The low-k board gives *average* in-use condition thermal performance and consists of a single trace layer 25 mm long and 2-oz thick copper. The high-k board gives *best case* in-use condition and consists of two 1-oz buried power planes with a single trace layer 25 mm long with 2-oz thick copper. A 4% to 50% difference in Θ_{JA} can be measured between these two test cards

Θ_{JC} (Junction-to-Case Thermal Resistance) is defined as difference in junction temperature to case divided by the operating power. It is measured by putting the mounted package up against a copper block cold plate to force heat to flow from die, through the mold compound into the copper block.

Θ_{JC} is a useful thermal characteristic when a heatsink is applied to package. It is NOT a useful characteristic to predict junction temperature as it provides pessimistic numbers if the case temperature is measured in a non-standard system and junction temperatures are backed out. It can be used with Θ_{JB} in 1-dimensional thermal simulation of a package system.

Θ_{JB} (Junction-to-Board Thermal Resistance) is defined to be the difference in the junction temperature and the PCB temperature at the center of the package (closest to the die) when the PCB is clamped in a cold-plate structure. Θ_{JB} is only defined for the high-k test card.

Θ_{JB} provides an overall thermal resistance between the die and the PCB. It includes a bit of the PCB thermal resistance (especially for BGA's with thermal balls) and can be used for simple 1-dimensional network analysis of package system (see Figure 21).

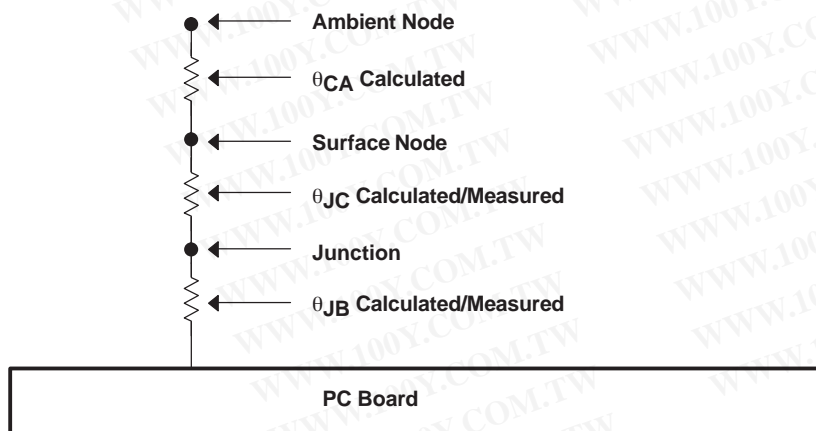
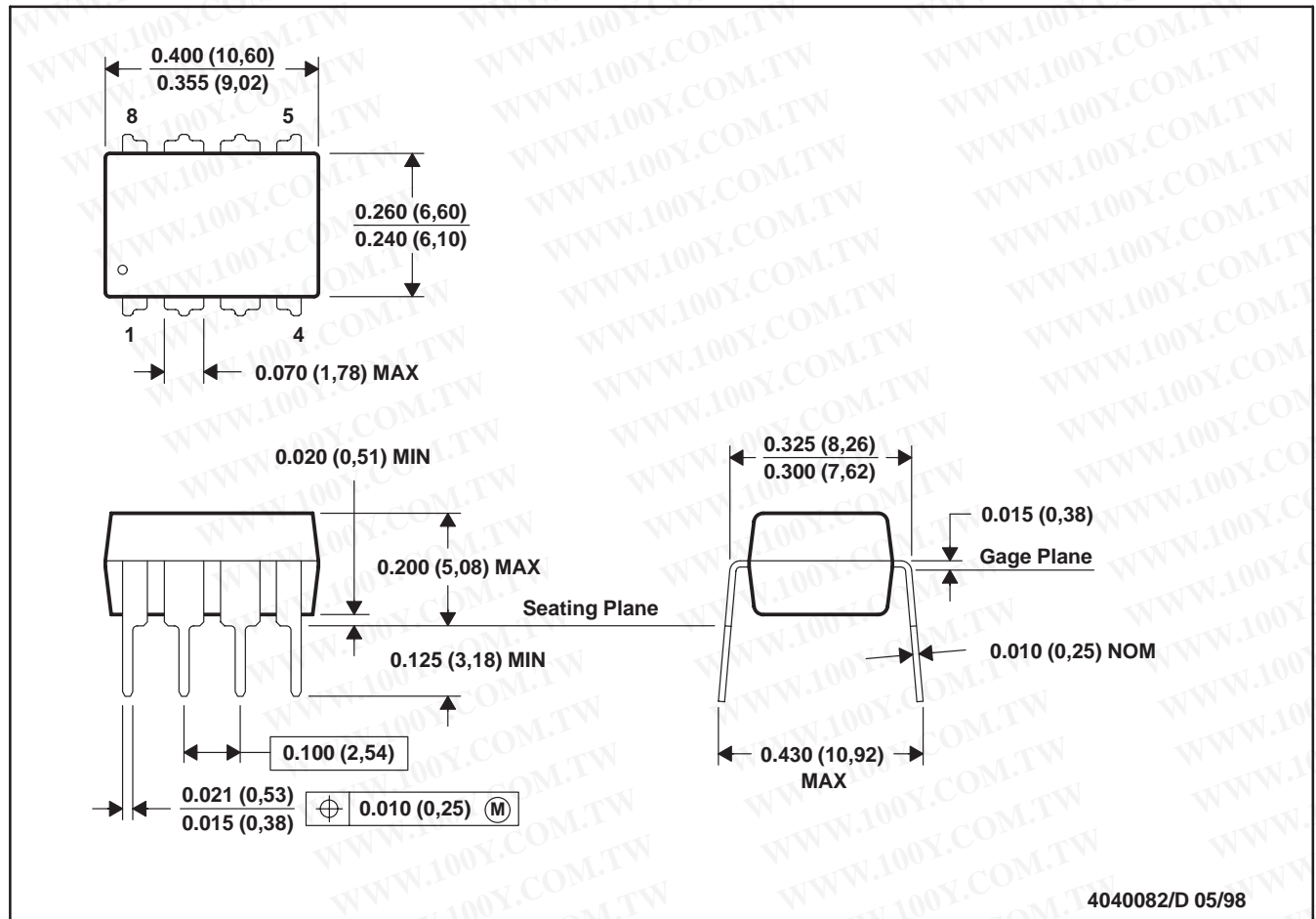


Figure 21. Thermal Resistance

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P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE



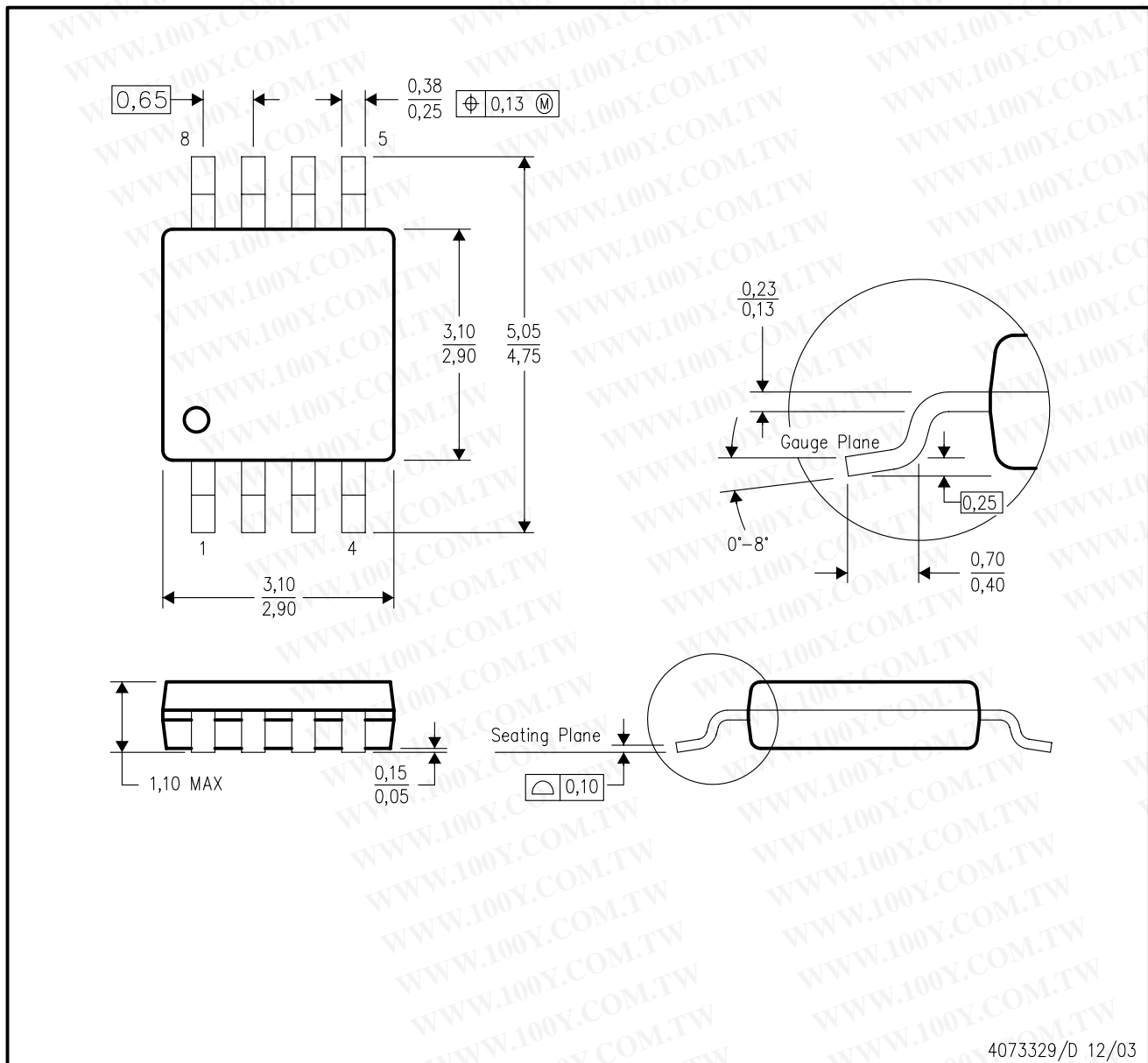
- NOTES: A. All linear dimensions are in inches (millimeters).
 B. This drawing is subject to change without notice.
 C. Falls within JEDEC MS-001

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For the latest package information, go to http://www.ti.com/sc/docs/package/pkg_info.htm

DGK (S-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE

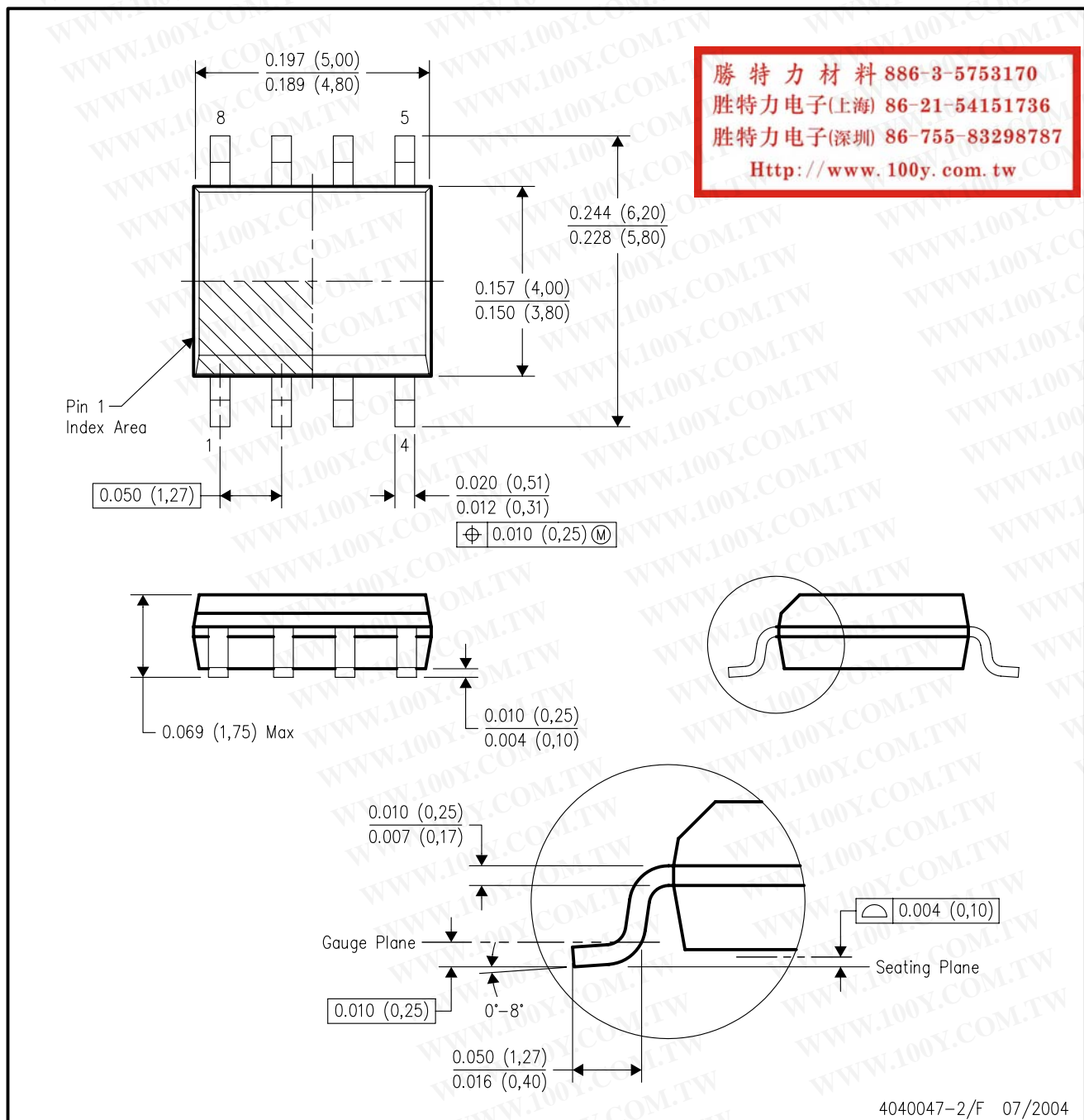


- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Body dimensions do not include mold flash or protrusion.
 - Falls within JEDEC MO-187 variation AA.

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D (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



4040047-2/F 07/2004

- NOTES:
- All linear dimensions are in inches (millimeters).
 - This drawing is subject to change without notice.
 - Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
 - Falls within JEDEC MS-012 variation AA.